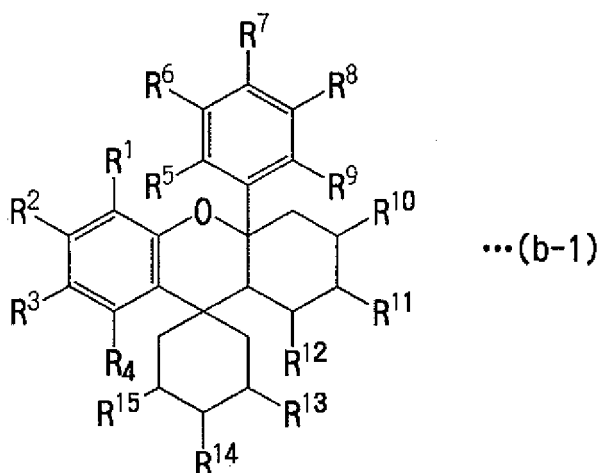


AMENDMENTS TO THE CLAIMS

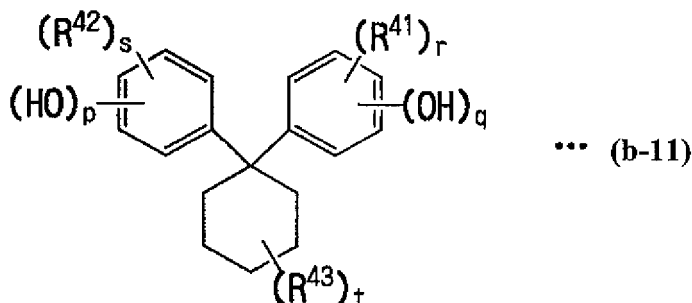
1. **(Previously Presented)** A positive photoresist composition comprising:

(A) an alkali-soluble novolak resin having a weight average molecular weight of 1,000 to 50,000, in which a portion of hydrogen atoms of phenolic hydroxyl groups are substituted with 1,2-naphthoquinonediazidesulfonyl groups; and

(B) a dissolution promoter comprising at least one compound selected from the group consisting of compounds represented by a general formula (b-1) and a general formula (b-11) shown below:



wherein, R¹ to R⁹ each represent, independently, a hydrogen atom, an alkyl group, a halogen atom, or a hydroxyl group, although at least one of R¹ to R⁹ represents a hydroxyl group; and R¹⁰ to R¹⁵ each represent, independently, a hydrogen atom, an alkyl group, an alkenyl group, a cycloalkyl group or an aryl group;



wherein, R^{41} to R^{43} each represent, independently, a lower alkyl group, a cycloalkyl group or a lower alkoxy group; p and q each represent an integer from 1 to 3; and r, s and t each represent either 0, or an integer from 1 to 3.

2. **(Original)** A positive photoresist composition according to claim 1, wherein said component (A) is a fractionated resin in which fractionation treatment has been used to reduce a lower molecular weight fraction to no more than 80% by weight of a value prior to said fractionation.

3. **(Original)** A positive photoresist composition according to claim 1, further comprising a photosensitizer (C).

4. **(Original)** A positive photoresist composition according to claim 1, which comprises both (b-1) and (b-11) as dissolution promoters.

5. **(Previously presented)** A method of forming a resist pattern comprising the steps of applying a positive photoresist composition according to any one of claim 1 through claim 4 to a substrate, conducting a prebake, performing selective exposure, and then performing alkali developing to form said resist pattern.

6. **(Previously presented)** The positive photoresist composition according to claim 1, wherein said component (A) has a weight average molecular weight of 2,000 to 20,000.

7. **(Previously presented)** The positive photoresist composition according to claim 3, wherein the quantity of said component (C) within said positive photoresist composition,

relative to the combined quantity of said component (A) and said component (B), is 30% by weight or less.

8. **(Previously presented)** The positive photoresist composition according to claim 1, wherein the proportion of the hydrogen atoms of the phenolic hydroxyl groups substituted with 1,2-naphthoquinonediazidesulfonyl groups within said component (A) is from 2 to 10 mol%.

9. **(New)** The positive photoresist composition according to claim 1, formed into a resist pattern on a substrate, wherein said resist pattern is at least 3 μm in thickness.